VS-HFA70EA120

Vishay Semiconductors



HEXFRED[®] Ultrafast Soft Recovery Diode, 70 A



PRODUCT SUMMARY					
V _R	1200 V				
V _F (typical)	2.2 V				
t _{rr} (typical)	48 ns				
$I_{F(DC)}$ at T_C , per module	70 A at 121 °C				
Package	SOT-227				

FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Antiparallel diodes
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION/APPLICATIONS

This SOT-227 modules with HEXFRED[®] rectifier are in antiparallel configuration. The antiparallel configuration is used for simple series rectifier and high voltage application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Cathode to anode voltage	V _R		1200	V		
Continuous forward current, per leg	١ _F	T _C = 121 °C	35	٨		
Single pulse forward current	I _{FSM}	$T_J = 25 \ ^{\circ}C$	350	A		
Maximum power dissipation, per leg	Р	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$	357	w		
Maximum power dissipation, per leg	PD	T _C = 100 °C	143			
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 minute	2500	V		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to 150	°C		

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-		
Forward voltage, per leg		I _F = 30 A	-	2.2	3.0		
	V _{FM}	I _F = 60 A	-	2.8	4.0	V	
		I _F = 30 A, T _J = 125 °C	-	2.13	-		
		I _F = 60 A, T _J = 125 °C	-	2.70	-		
		I _F = 30 A, T _J = 150 °C	-	2.04	-	1	
		I _F = 60 A, T _J = 150 °C	-	2.65	-		
	I _{RM}	$V_{R} = V_{R}$ rated	-	2.0	75	μA	
Reverse leakage current, per leg		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1.6	5	mA	
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	5	10	IIIA	

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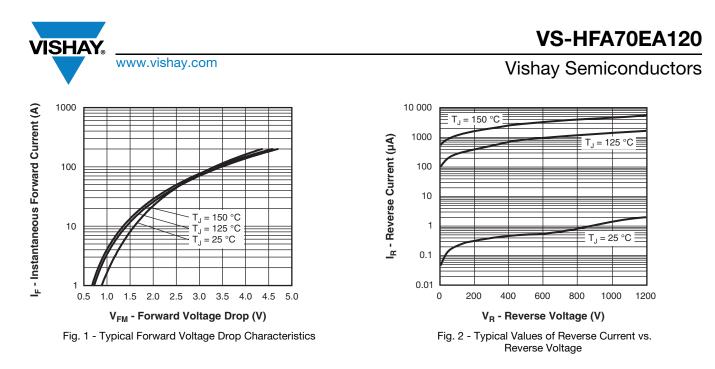




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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST	MIN.	TYP.	MAX.	UNITS		
		I _F = 1 A; dI _F /d	t = 200 A/ μ s; V _R = 30 V	-	48	-		
Reverse recovery time, per leg	t _{rr}	$T_J = 25 \ ^\circ C$		-	145	-	ns	
		T _J = 125 °C	$I_{\rm F} = 50 {\rm A}$	-	218	-	1	
Deels receiver a current per les		T _J = 25 °C		-	13	-	^	
Peak recovery current, per leg	I _{RRM}	T _J = 125 °C	dI _F /dt = - 200 A/µs V _B = 200 V	-	19	-	A	
	Q _{rr}	$T_J = 25 \ ^\circ C$	VR - 200 V	-	910	-	nC	
Reverse recovery charge, per leg Q		T _J = 125 °C		-	1920	-	nc	
Junction capacitance, per leg	CT	V _R = 1200 V		-	27	-	pF	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Junction to case, single leg conducting	Б		-	-	0.35		
Junction to case, both legs conducting	– R _{thJC}		-	-	0.175	°C/W	
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-		
Weight			-	30	-	g	
Mounting torque			-	-	1.3	Nm	
Case style				SOT	-227		



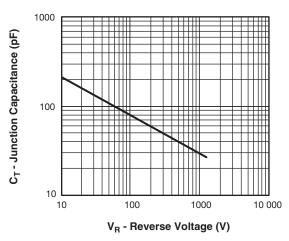


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

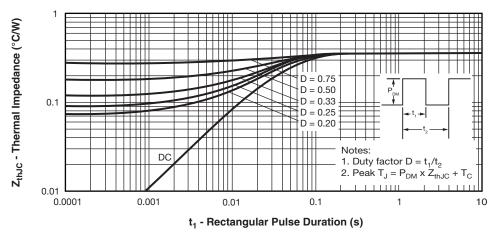
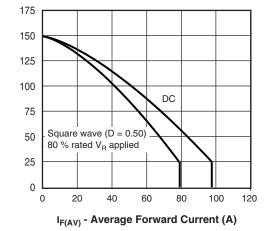


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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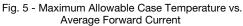
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SHAY

Allowable Case Temperature (°C)



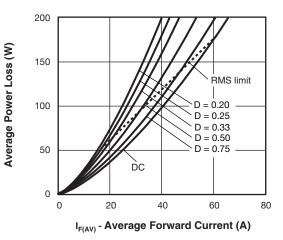


Fig. 6 - Forward Power Loss Characteristics

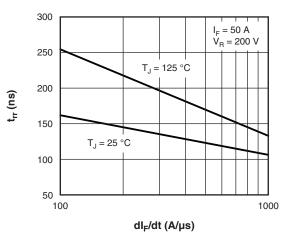


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

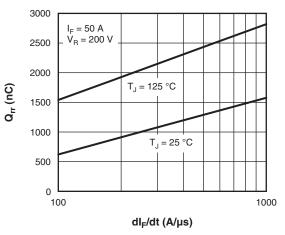
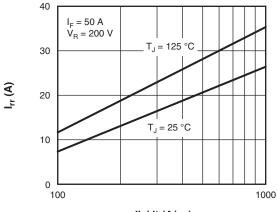


Fig. 8 - Typical Stored Charge vs. dl_F/dt



dl_F/dt (A/µs)

Fig. 9 - Typical Peak Recovery Current vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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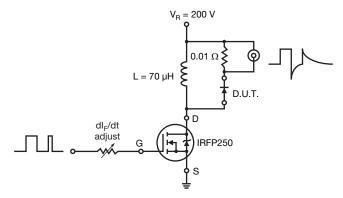


Fig. 10 - Reverse Recovery Parameter Test Circuit

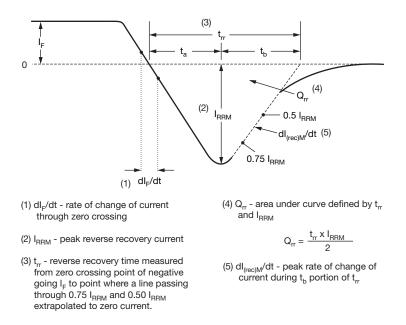


Fig. 11 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	70	Е	Α	120	
		2	3	4	5	6	7	-
	1 -	- Vishay Semiconductors product						
	2 -	HEX	HEXFRED [®] family					
	3 -	Pro	Process designator (A = Electron irradiated)					
	4 -	Ave	Average current (70 = 70 A)					
	5 -	Circ	Circuit configuration (2 separate diodes, antiparallel pin-out)					
	6 -	Pac	Package indicator (SOT-227 standard insulated base)					
	7 -	Volt	Voltage rating (120 = 1200 V)					

CIRCUIT CON	CIRCUIT CONFIGURATION							
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING						
			Lead Assignment					
2 separate diodes, antiparallel pin-out	E							

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95423					
Part marking information	www.vishay.com/doc?95425				



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